Is Now Part of

ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

FAIRCHILD

August 2015

FDMS8095AC

Dual N & P-Channel PowerTrench® MOSFET
N-Channel: 150 V, 27 A, 30 mΩ P-Channel: -150 V, -2.2 A, 1200 mΩ

Features

Q1: N-Channel

- Max $r_{DS(on)}$ = 30 mΩ at V_{GS} = 10 V, I_D = 6.2 A
- Max $r_{DS(on)}$ = 41 mΩ at V_{GS} = 6 V, I_D = 5.2 A

Q2: P-Channel

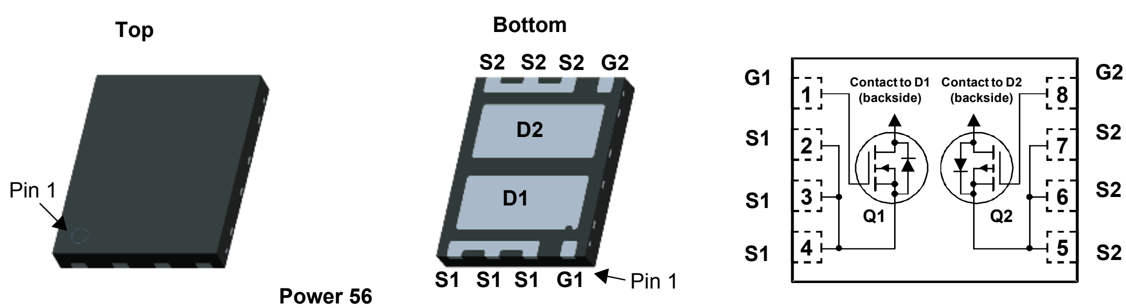
- Max $r_{DS(on)}$ = 1200 mΩ at V_{GS} = -10 V, I_D = -1 A
- Max $r_{DS(on)}$ = 1400 mΩ at V_{GS} = -6 V, I_D = -0.9 A
- Optimised for active clamp forward converters
- RoHS Compliant

General Description

These dual N and P-Channel enhancement mode Power MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench® process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance. Shrinking the area needed for implementation of active clamp topology; enabling best in class power density.

Applications

- DC-DC Converter
- Active Clamp



MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter			Q1	Q2	Units
V_{DS}	Drain to Source Voltage			150	-150	V
V_{GS}	Gate to Source Voltage			±20	±25	V
I_D	Drain Current -Continuous	T_C = 25 °C	(Note 5)	27	-2.2	A
	Drain Current -Continuous	T_C = 100 °C	(Note 5)	17	-1.4	
	-Continuous	T_A = 25 °C		6.2 [1a]	-1 [1b]	
	-Pulsed		(Note 4)	143	-8.8	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	216	6	mJ
P_D	Power Dissipation for Single Operation	T_A = 25 °C		2.3 [1a]	2.3 [1b]	W
	Power Dissipation for Single Operation	T_A = 25 °C		0.9 [1c]	0.9 [1d]	
	Power Dissipation for Single Operation	T_C = 25 °C		50	12.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150		°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	55 [1a]	55 [1b]	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	138 [1c]	138 [1d]	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.5	10	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS8095AC	FDMS8095AC	Power 56	13"	12 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

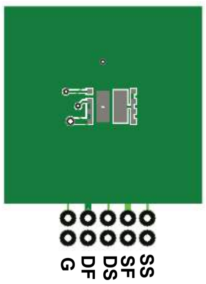
Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Off Characteristics							
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V I_D = -250 μA, V_{GS} = 0 V	Q1 Q2	150 -150			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C I_D = -250 μA, referenced to 25 °C	Q1 Q2		103 122		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 120 V, V_{GS} = 0 V V_{DS} = -120 V, V_{GS} = 0 V	Q1 Q2			1 -1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V V_{GS} = ±25 V, V_{DS} = 0 V	Q1 Q2			±100 ±100	nA nA
On Characteristics							
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA V_{GS} = V_{DS}, I_D = -250 μA	Q1 Q2	2.0 -2.0	3.2 -3.2	4.0 -4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C I_D = -250 μA, referenced to 25 °C	Q1 Q2		-11 -6		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 6.2 A V_{GS} = 6 V, I_D = 5.2 A V_{GS} = 10 V, I_D = 6.2 A, T_J = 125 °C	Q1		25 33 48	30 41 58	mΩ
		V_{GS} = -10 V, I_D = -1 A V_{GS} = -6 V, I_D = -0.9 A V_{GS} = -10 V, I_D = -1 A, T_J = 125 °C	Q2		840 940 1520	1200 1400 2171	
g_{FS}	Forward Transconductance	V_{DD} = 10 V, I_D = 6.2 A V_{DD} = -10 V, I_D = -1 A	Q1 Q2		19 0.75		S
Dynamic Characteristics							
C_{iss}	Input Capacitance	Q1 V_{DS} = 75 V, V_{GS} = 0 V, f = 1 MHZ Q2 V_{DS} = -75 V, V_{GS} = 0 V, f = 1 MHZ	Q1 Q2		1441 162	2020 230	pF
C_{oss}	Output Capacitance		Q1 Q2		127 13	180 25	pF
C_{rss}	Reverse Transfer Capacitance		Q1 Q2		4.4 0.6	10 5	pF
R_g	Gate Resistance		Q1 Q2	0.1 0.1	1.3 3.3	3.3 8.3	Ω
Switching Characteristics							
$t_{d(on)}$	Turn-On Delay Time	Q1 V_{DD} = 75 V, I_D = 6.2 A, V_{GS} = 10 V, R_{GEN} = 6 Ω Q2 V_{DD} = -75 V, I_D = -1 A, V_{GS} = -10 V, R_{GEN} = 6 Ω	Q1 Q2		12 5.2	22 11	ns
t_r	Rise Time		Q1 Q2		2.7 1.6	10 10	ns
$t_{d(off)}$	Turn-Off Delay Time		Q1 Q2		18 7.4	33 15	ns
t_f	Fall Time		Q1 Q2		4 6.3	10 13	ns
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0 V to 10 V V_{GS} = 0 V to -10 V; Q1: V_{DD} = 75 V, I_D = 6.2 A; Q2: V_{DD} = -75 V, I_D = -1 A	Q1 Q2		21 2.8	30 4	nC
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0 V to 6 V V_{GS} = 0 V to -6 V	Q1 Q2		13 1.8	19 2.6	nC
Q_{gs}	Gate to Source Charge		Q1 Q2		6.7 0.8		nC
Q_{gd}	Gate to Drain "Miller" Charge		Q1 Q2		3.9 0.7		nC

Electrical Characteristics T_J = 25 °C unless otherwise noted

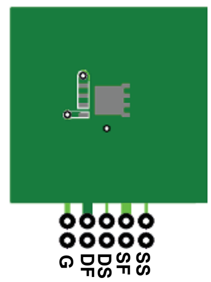
Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Drain-Source Diode Characteristics							
V_{SD}	Source-Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 6.2 A (Note 2) V_{GS} = 0 V, I_S = -1 A (Note 2)	Q1 Q2		0.8 -0.9	1.3 -1.3	V
t_{rr}	Reverse Recovery Time	Q1 I_F = 6.2 A, di/dt = 100 A/s	Q1 Q2		69 44	111 71	ns
Q_{rr}	Reverse Recovery Charge	Q2 I_F = -1 A, di/dt = 100 A/s	Q1 Q2		106 68	170 109	nC

Notes:

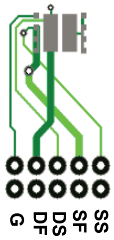
1. $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta CA}$ is determined by the user's board design.



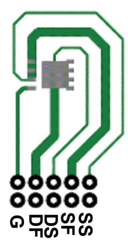
a. 55 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b. 55 °C/W when mounted on a 1 in^2 pad of 2 oz copper



c. 138 °C/W when mounted on a minimum pad of 2 oz copper



d. 138 °C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 µs, Duty cycle < 2.0%.

3. Q1: E_{AS} of 216 mJ is based on starting T_J = 25 ^oC, L = 3 mH, I_{AS} = 12 A, V_{DD} = 150 V, V_{GS} = 10 V. 100% test at L = 0.3 mH, I_{AS} = 28 A.

Q2: E_{AS} of 6 mJ is based on starting T_J = 25 ^oC, L = 3 mH, I_{AS} = -2 A, V_{DD} = -150 V, V_{GS} = -10 V. 100% test at L = 0.3 mH, I_{AS} = -6.9 A.

4. Pulsed Id please refer to Fig 11 SOA graph for more details.

5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

Typical Characteristics (Q1 N-Channel) T_J = 25°C unless otherwise noted

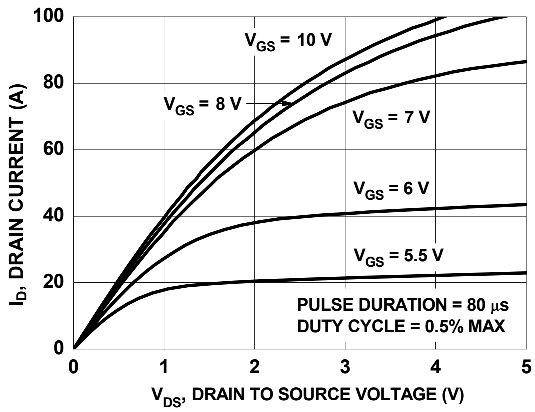


Figure 1. On Region Characteristics

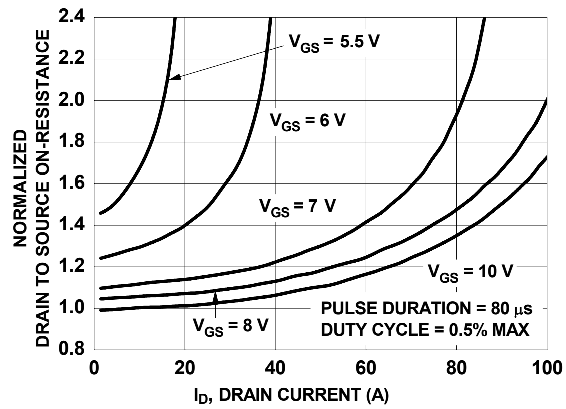


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

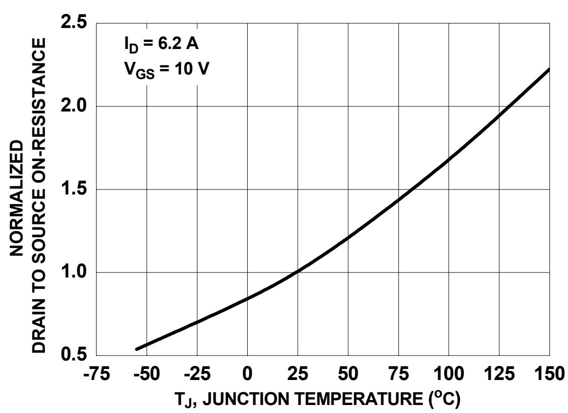


Figure 3. Normalized On Resistance vs Junction Temperature

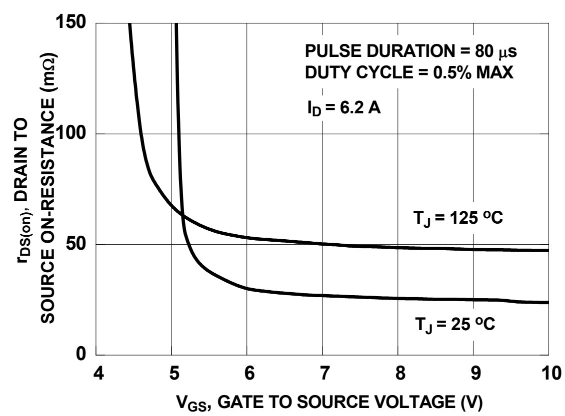


Figure 4. On-Resistance vs Gate to Source Voltage

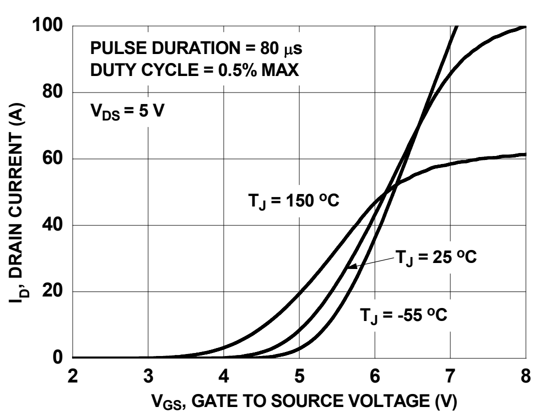


Figure 5. Transfer Characteristics

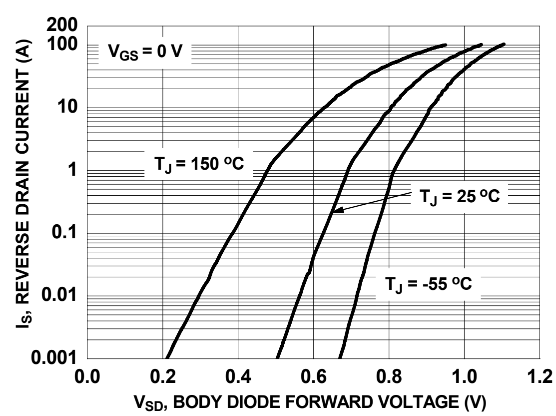


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics (Q1 N-Channel) T_J = 25°C unless otherwise noted

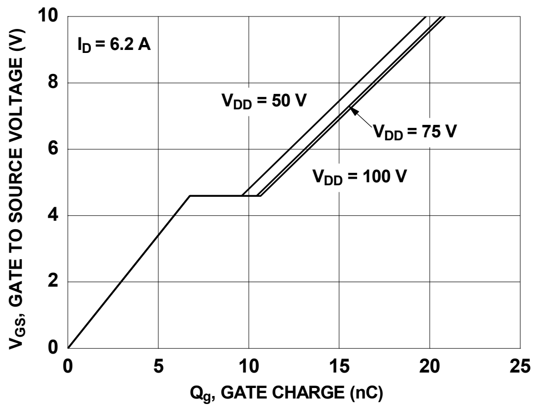


Figure 7. Gate Charge Characteristics

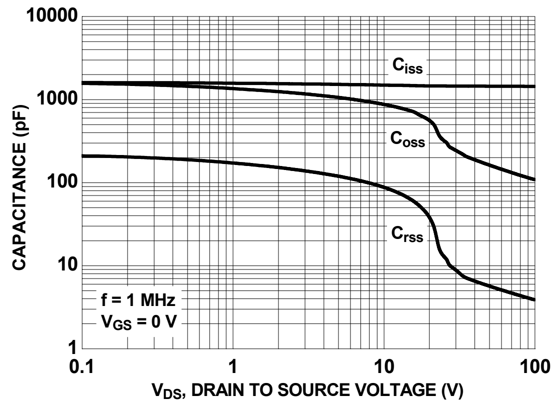


Figure 8. Capacitance vs Drain to Source Voltage

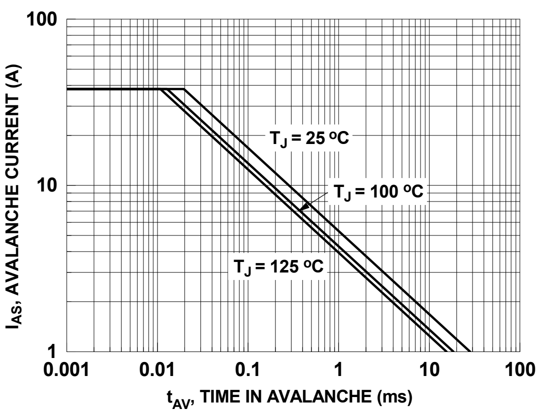


Figure 9. Unclamped Inductive Switching Capability

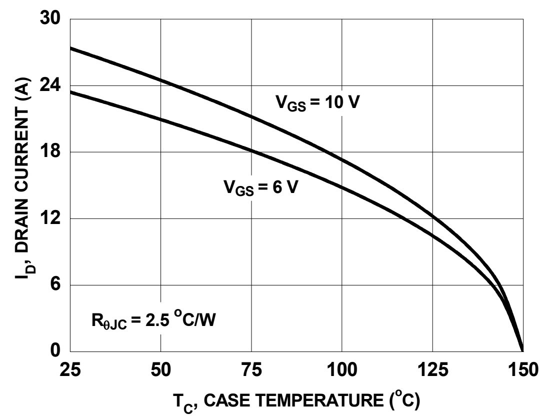


Figure 10. Maximum Continuous Drain Current vs Case Temperature

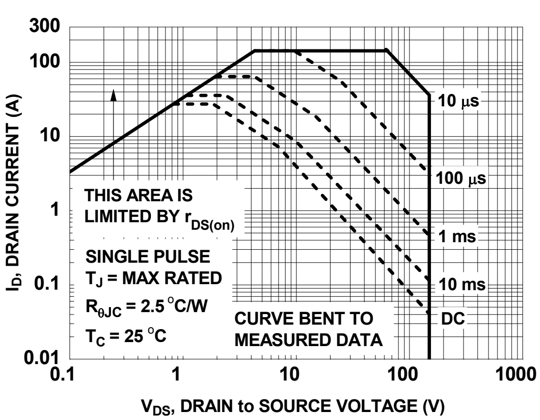


Figure 11. Forward Bias Safe Operating Area

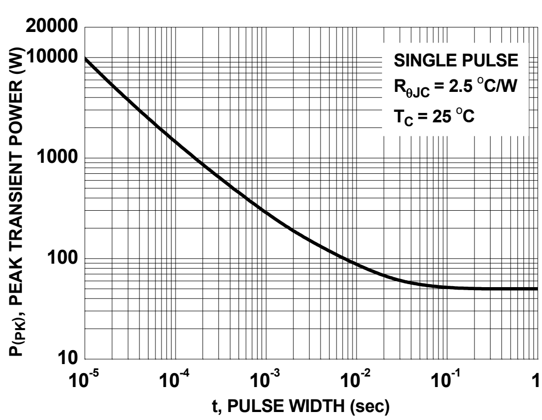


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics (Q1 N-Channel) T_J = 25°C unless otherwise noted

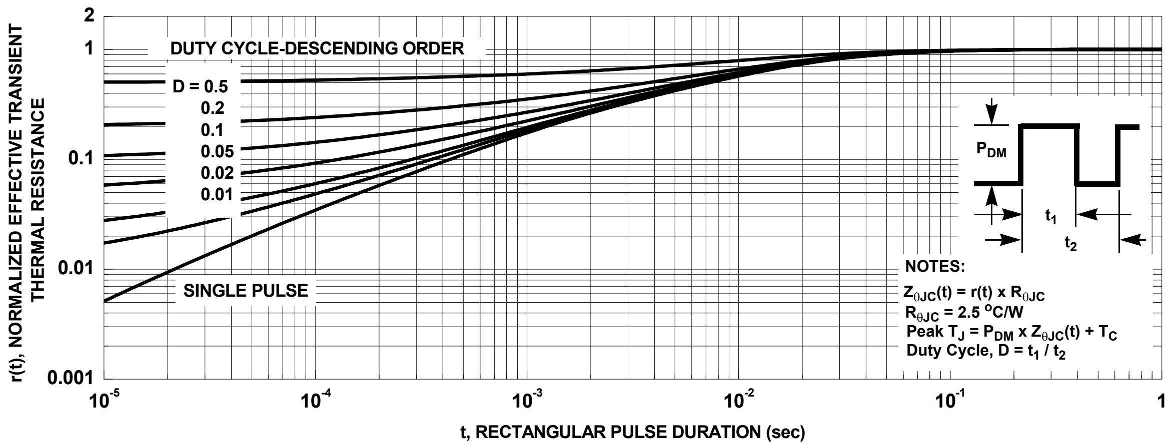


Figure 13. Junction-to-Case Transient Thermal Response Curve

Typical Characteristics (Q2 P-Channel) T_J = 25 °C unless otherwise noted

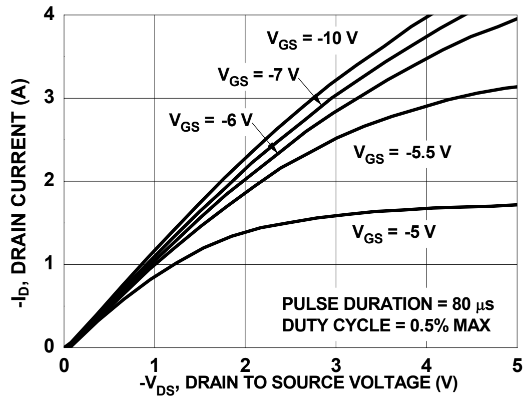


Figure 14. On- Region Characteristics

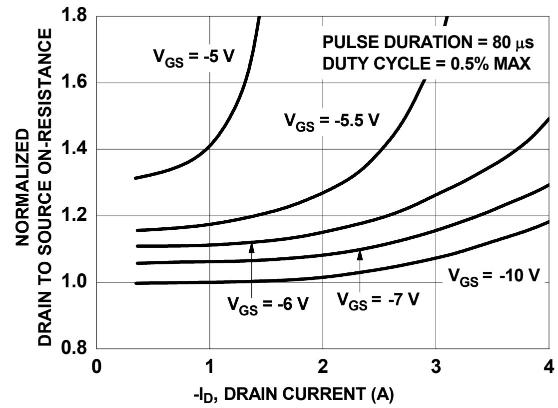


Figure 15. Normalized on-Resistance vs Drain Current and Gate Voltage

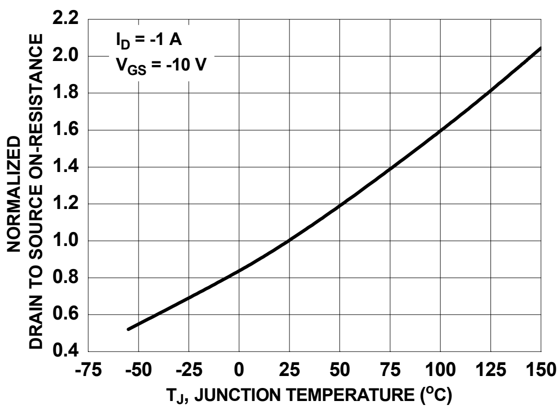


Figure 16. Normalized On-Resistance vs Junction Temperature

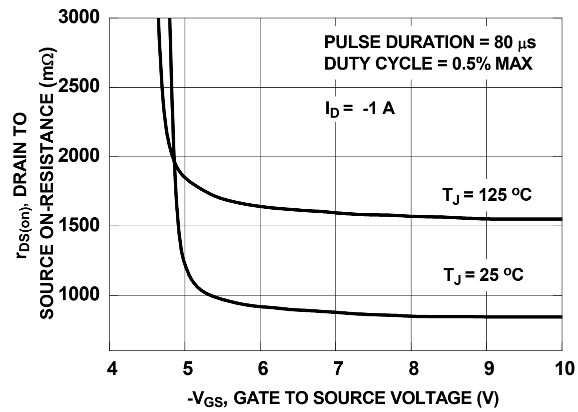


Figure 17. On-Resistance vs Gate to Source Voltage

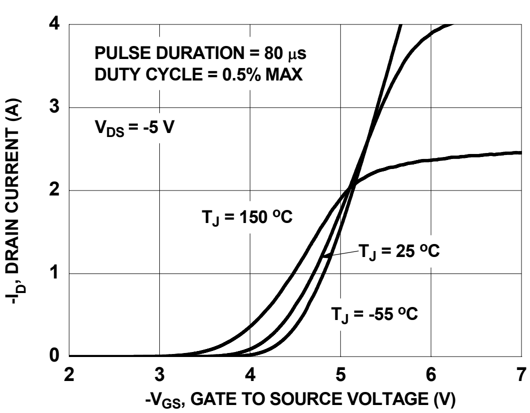


Figure 18. Transfer Characteristics

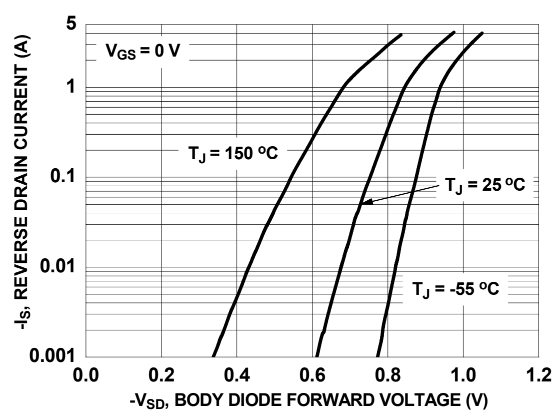


Figure 19. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics (Q2 P-Channel) T_J = 25°C unless otherwise noted

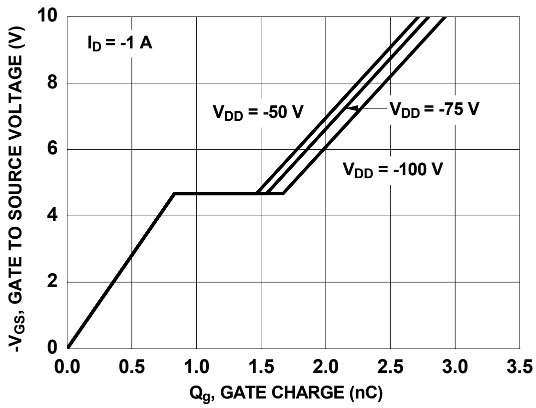


Figure 20. Gate Charge Characteristics

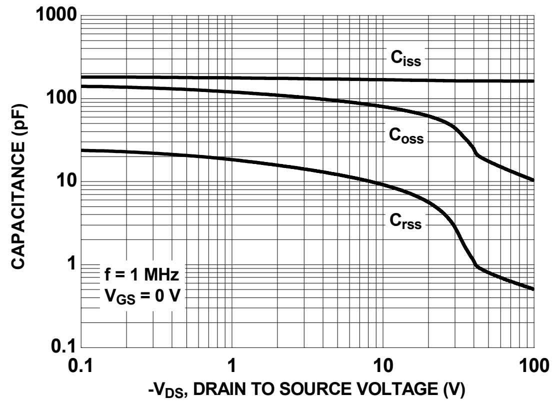


Figure 21. Capacitance vs Drain to Source Voltage

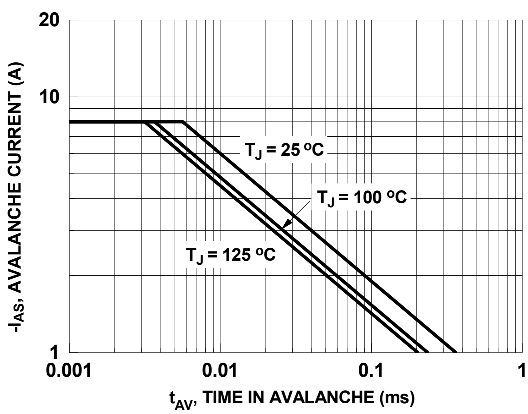


Figure 22. Unclamped Inductive Switching Capability

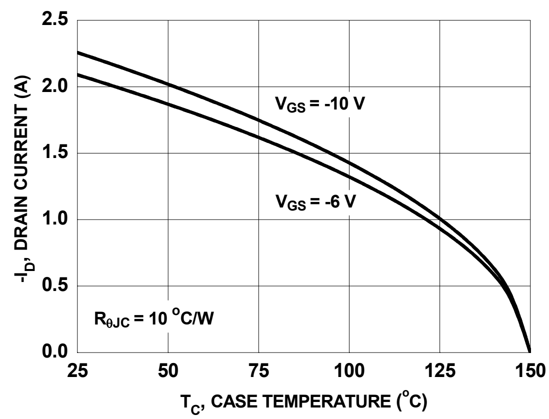


Figure 23. Maximum Continuous Drain Current vs Case Temperature

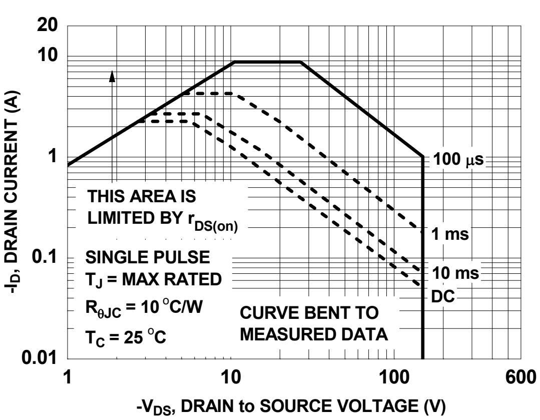


Figure 24. Forward Bias Safe Operating Area

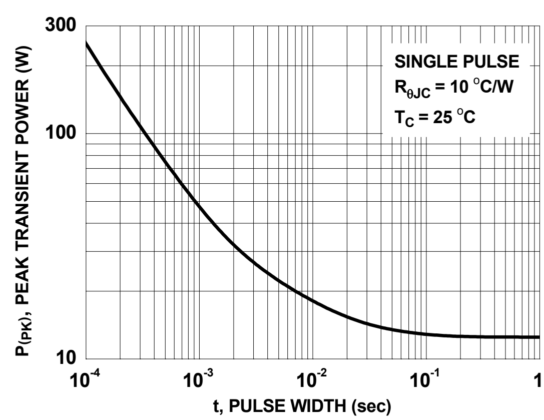


Figure 25. Single Pulse Maximum Power Dissipation

Typical Characteristics (Q2 P-Channel) T_J = 25 °C unless otherwise noted

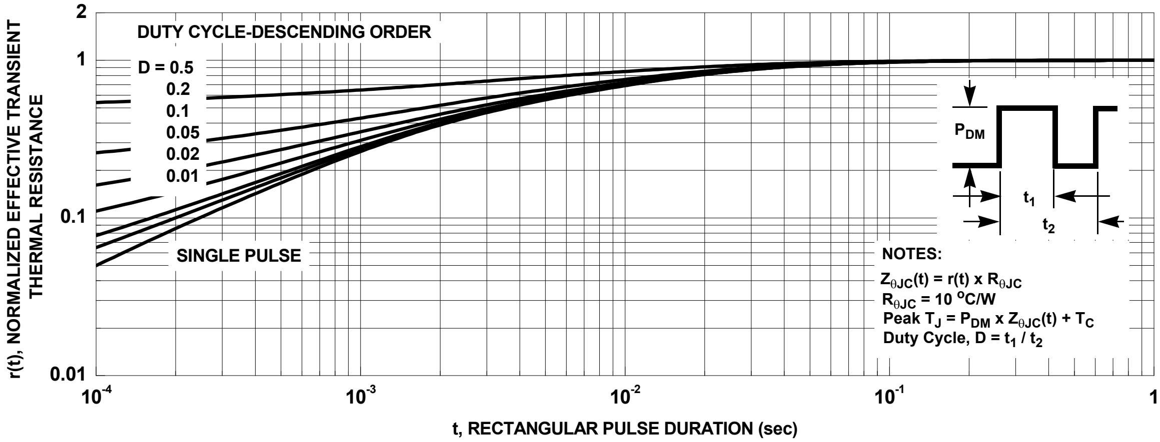
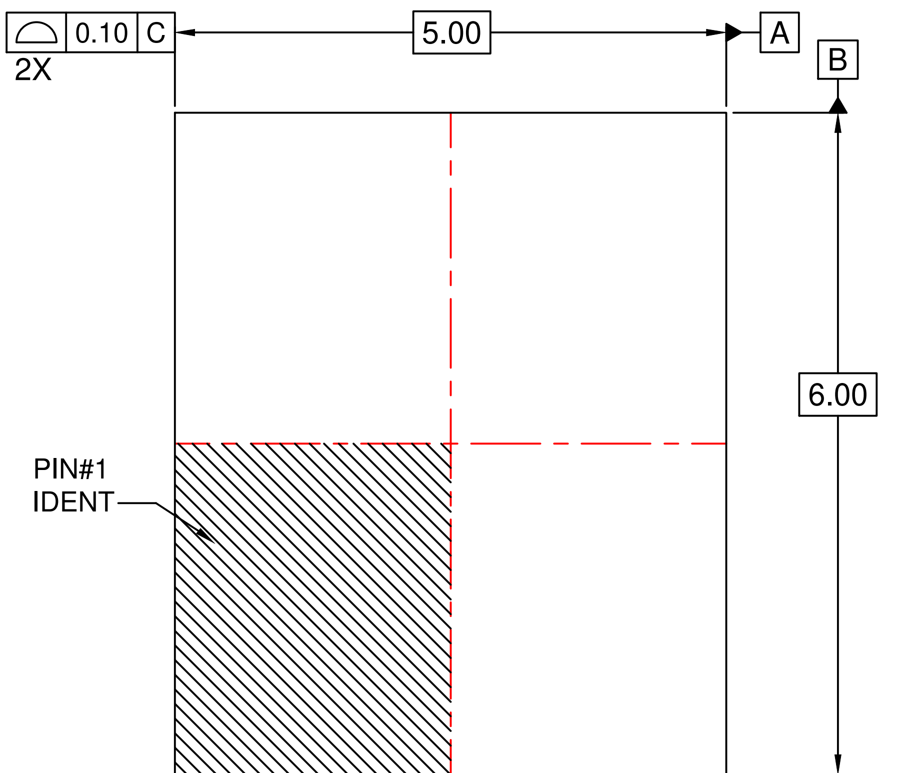
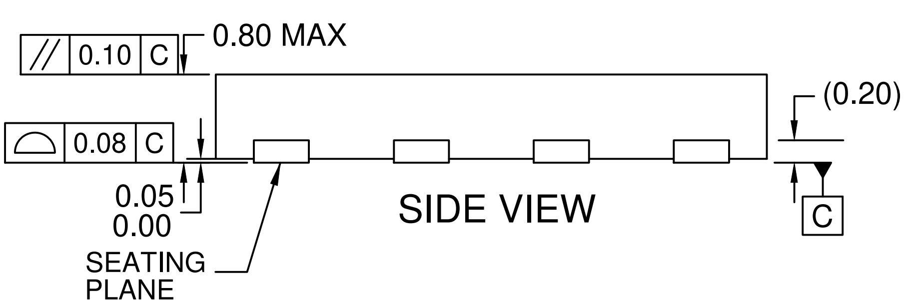


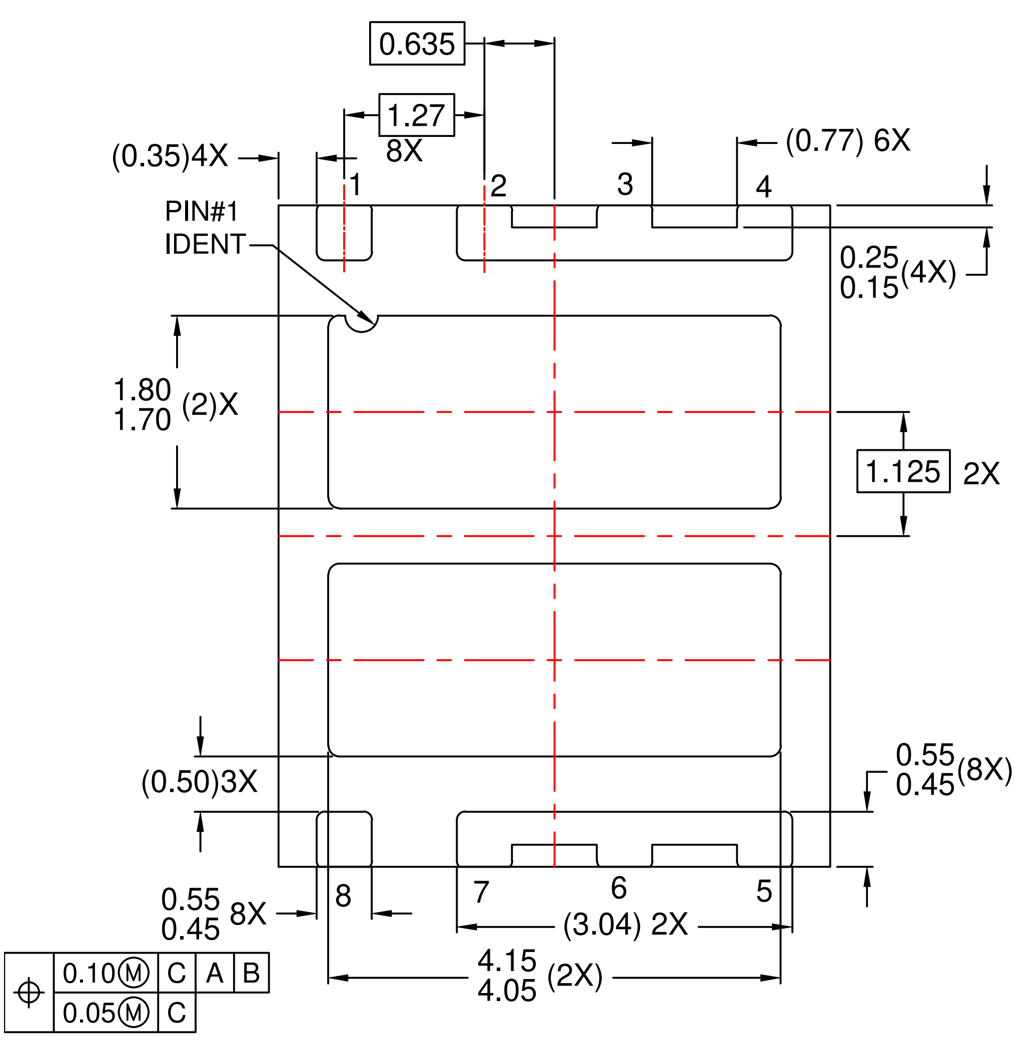
Figure 26. Junction-to-Case Transient Thermal Response Curve



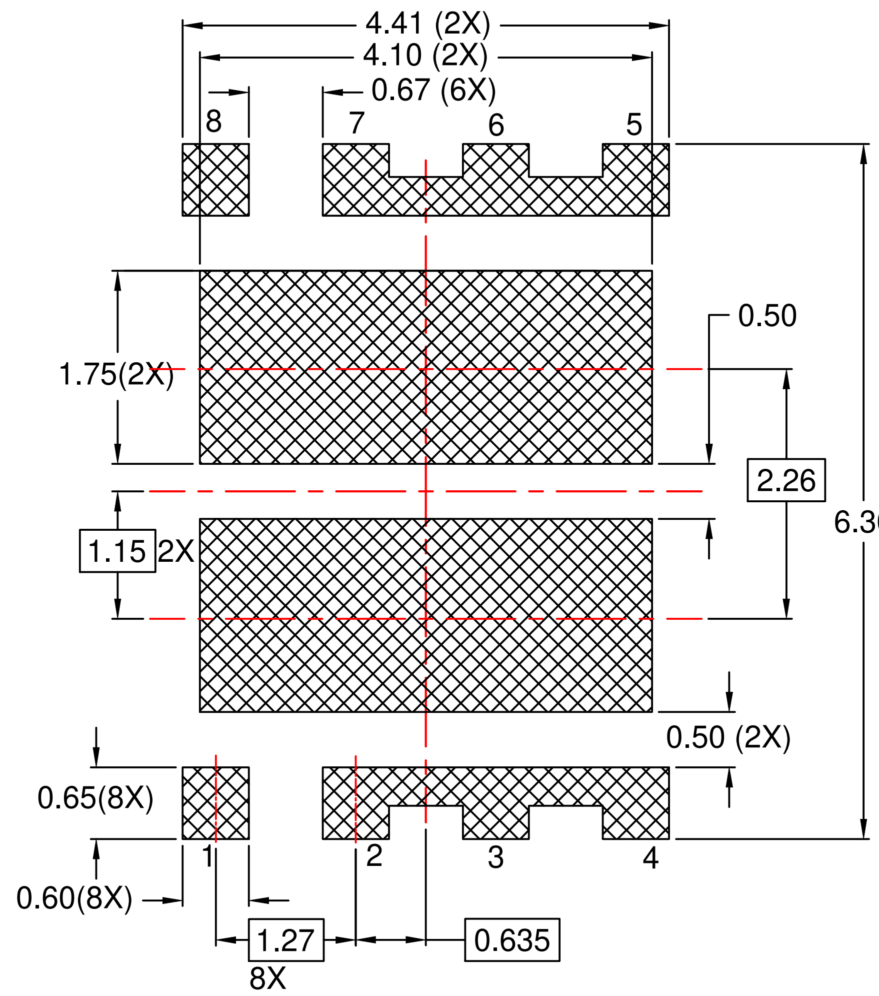
TOP VIEW



SIDE VIEW



BOTTOM VIEW



RECOMMENDED LAND PATTERN

NOTES:

A. DOES NOT FULLY CONFORM TO JEDEC REGISTRATION, MO-229.

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.

D. LAND PATTERN RECOMMENDATION IS BASED ON FSC DESIGN ONLY.

E. DRAWING FILENAME: MKT-MLP08Zrev1.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative